



July 2008
Power-SPM™

FP7G75US60

Transfer Molded Type IGBT Module

General Description

Fairchild's New IGBT Modules (Transfer Molded Type) provide low conduction and switching losses as well as short circuit ruggedness. They are designed for applications such as Motor control, Uninterrupted Power Supplies (UPS) and general Inverters where short circuit ruggedness is a required feature.

Features

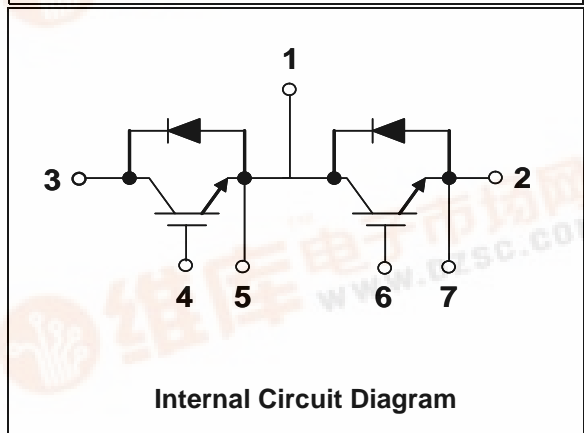
- Short Circuit rated 10us @Tc=100°C, Vge=15V
- High Speed Switching
- Low Saturation Voltage : Vce(sat) =2.2V @Ic=75A
- High Input Impedance
- Fast & Soft Anti-Parallel FWD

Application

- Welders
- AC & DC Motor Controls
- General Purpose Inverters
- Robotics
- Servo Controls
- UPS



Package Code : EPM7



Internal Circuit Diagram

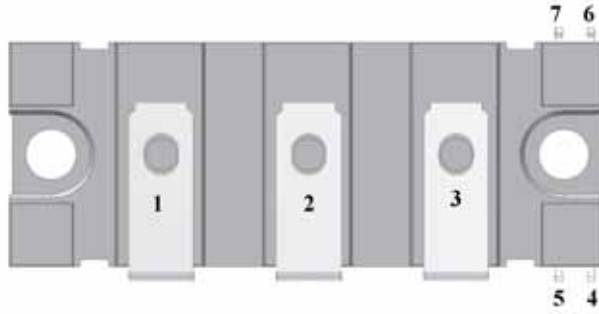
Absolute Maximum Ratings

Symbol	Description	Rating	Units
V _{CES}	Collector-Emitter Voltage	600	V
V _{GES}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current @ T _C = 25°C	75	A
I _{CM (1)}	Pulsed Collector Current	150	A
I _F	Diode Continuous Forward Current @ T _C = 100°C	75	A
I _{FM}	Diode Maximum Forward Current	150	A
T _{SC}	Short Circuit Withstand Time @ T _C = 100°C	10	us
P _D	Maximum Power Dissipation @ T _C = 25°C	310	W
T _J	Operating Junction Temperature	-40 to +125	°C
T _{stg}	Storage Temperature Range	-40 to +125	°C
V _{iso}	Isolation Voltage @ AC 1minute	2500	V
Mounting Torque	Power Terminals Screw : M5	2.0	N.m
	Mounting Screw : M5	2.0	N.m

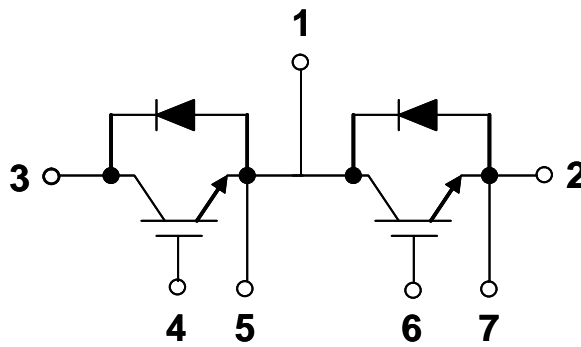
FP7G75US60 Transfer Molded Type IGBT Module



Pin Configuration and Pin Description



Top View



Internal Circuit Diagram

Pin Description

Pin Number	Pin Description
1	Emitter of Q1, IGBT, Collector of Q2, IGBT
2	Emitter of Q2, IGBT
3	Collector of Q1, IGBT
4	Gate of Q1, IGBT
5	Emitter of Q1, IGBT
6	Gate of Q2, IGBT
7	Emitter of Q2, IGBT

Electrical Characteristics ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coeff. of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	-	0.6	-	V
I_{CES}	Collector Cut-off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	250	μA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$V_{GE} = 0V, I_C = 75mA$	5.0	6.0	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 75A, V_{GE} = 15V$	-	2.2	2.8	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	-	4515	-	μF
C_{oes}	Output Capacitance		-	550	--	μF
C_{res}	Reverse Capacitance		-	100	-	μF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 75A,$ $R_G = 3.3\Omega, V_{GE} = 15V$ Inductive Load, $T_C = 25^\circ\text{C}$	-	33	-	ns
t_r	Rise Time		-	29	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	92	-	ns
t_f	Fall Time		-	91	-	ns
E_{on}	Turn-On Switching Loss		-	0.75	-	mJ
E_{off}	Turn-Off Switching Loss		-	0.72	-	mJ
E_{ts}	Total Switching Loss	-	1.47	-	mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 75A,$ $R_G = 3.3\Omega, V_{GE} = 15V$ Inductive Load, $T_C = 125^\circ\text{C}$	-	27	-	ns
t_r	Rise Time		-	22	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	96	-	ns
t_f	Fall Time		-	197	-	ns
E_{on}	Turn-On Switching Loss		-	0.73	-	mJ
E_{off}	Turn-Off Switching Loss		-	1.47	-	mJ
E_{ts}	Total Switching Loss	-	2.2	-	mJ	
T_{sc}	Short Circuit Withstand Time	$V_{CC} = 300V, V_{GE} = 15V @ T_C = 100^\circ\text{C}$	10	-	-	μs
Q_g	Total Gate Charge	$V_{CE} = 300V, I_C = 75A, V_{GE} = 15V$	-	205	-	nC
Q_{ge}	Gate-Emitter Charge		-	40	-	nC
Q_{gc}	Gate-Collector Charge		-	115	-	nC

Electrical Characteristics of DIODE ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
V_{FM}	Diode Forward Voltage	$I_F = 75\text{A}$	$T_C = 25^\circ\text{C}$	-	1.9	2.8	V
			$T_C = 100^\circ\text{C}$	-	1.8	-	
t_{rr}	Diode Reverse Recovery Time		$T_C = 25^\circ\text{C}$	-	78	112	ns
			$T_C = 100^\circ\text{C}$	-	156		
I_{rr}	Diode Peak Reverse Recovery Current	$I_F = 75\text{A}$ $di / dt = 150 \text{ A/us}$	$T_C = 25^\circ\text{C}$	-	5.7	7.5	A
			$T_C = 100^\circ\text{C}$	-	10		
Q_{rr}	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	-	222		nC
			$T_C = 100^\circ\text{C}$	-	780		

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/2 Module)	-	0.32	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/2 Module)	-	0.9	$^\circ\text{C/W}$
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.05	-	$^\circ\text{C/W}$
Weight	Weight of Module	-	90	g

Typical Performance Characteristics

Fig 1. Typical Output Characteristics

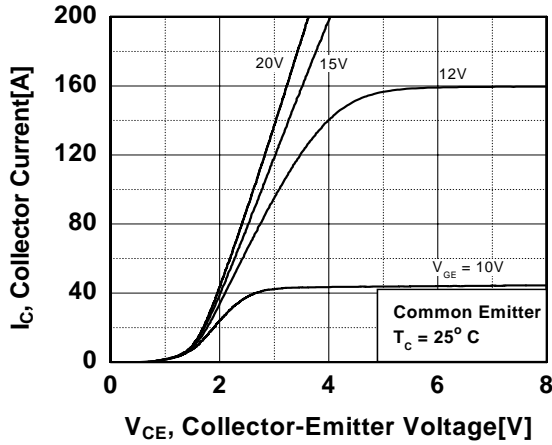


Fig 2. Typical Saturation Voltage Characteristics

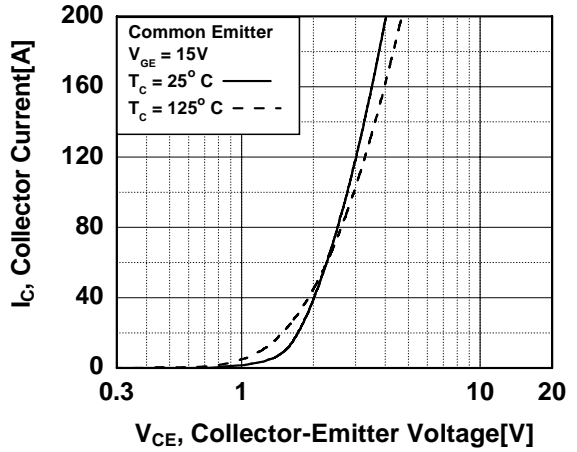


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

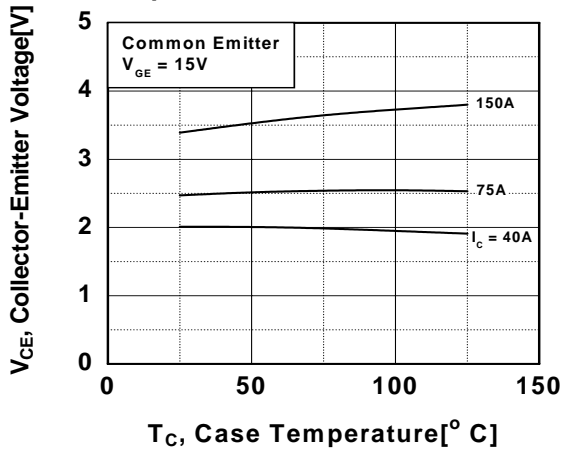


Fig 4. Load Current vs. Frequency

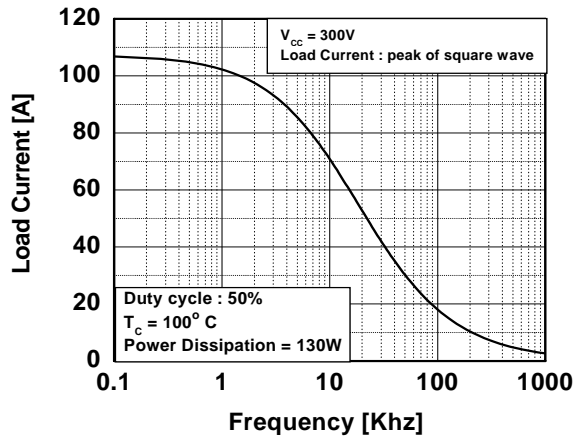


Fig 5. Saturation Voltage vs. V_{GE}

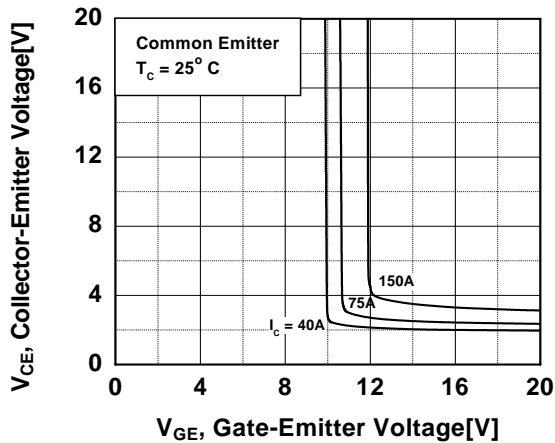


Fig 6. Saturation Voltage vs. V_{GE}

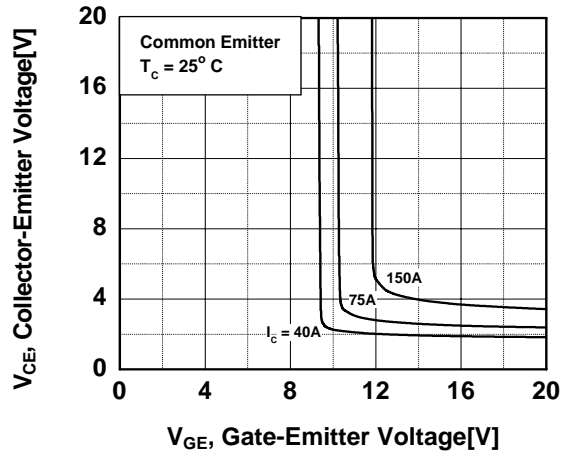


Fig 7. Capacitance Characteristics

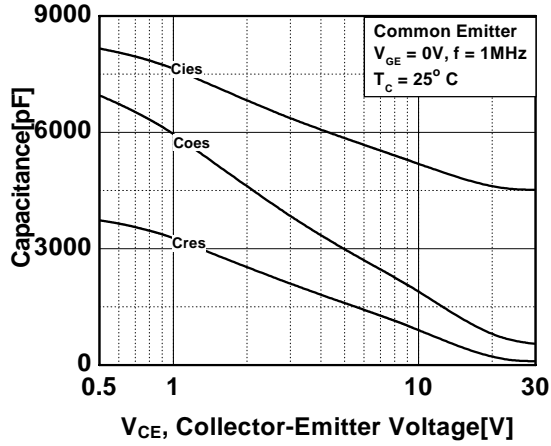


Fig 8. Turn-On Characteristics vs. Gate Resistance

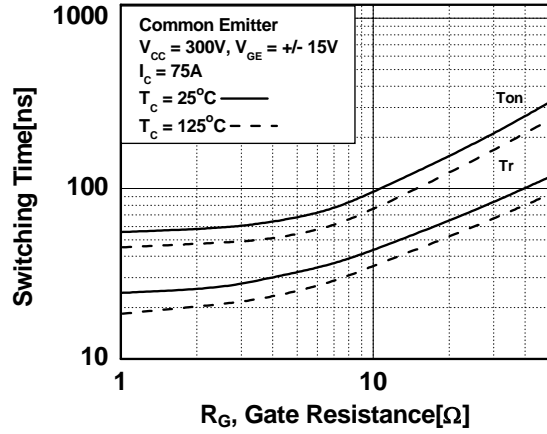


Fig 9. Turn-Off Characteristics vs. Gate Resistance

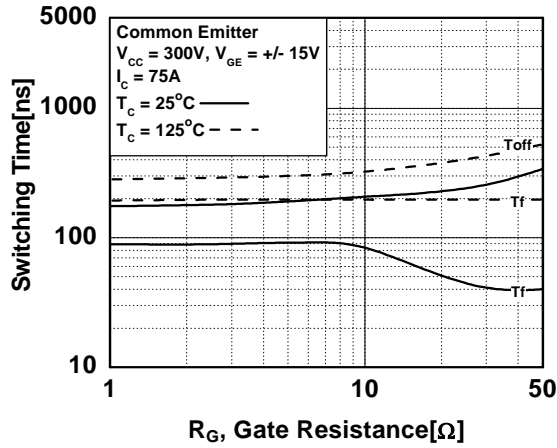


Fig 10. Switching Loss vs. Gate Resistance

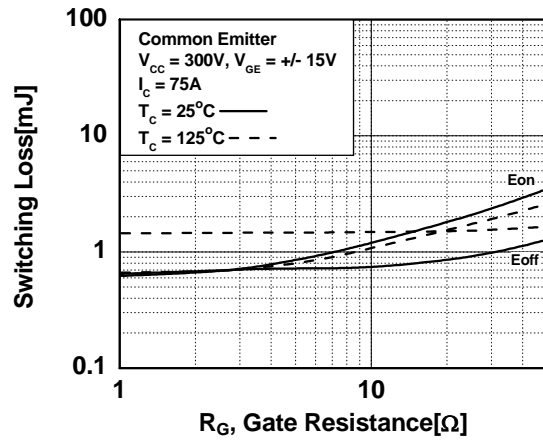


Fig 11. Turn-On Characteristics vs. Collector Current

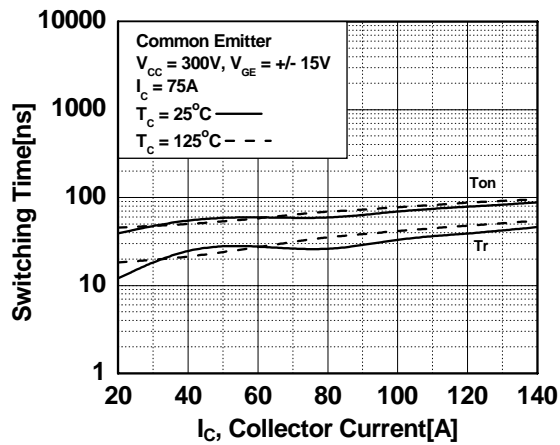


Fig 12. Turn-Off Characteristics vs. Collector Current

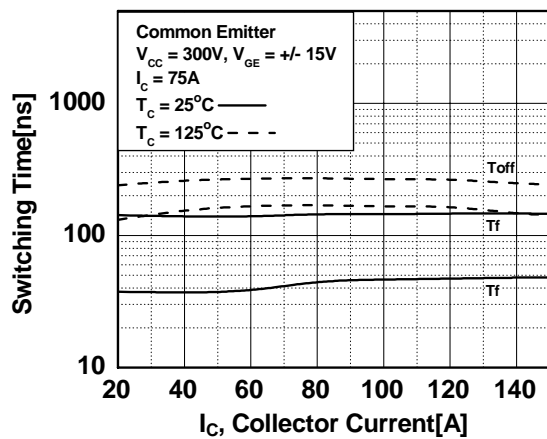


Fig 13. Switching Loss vs. Collector

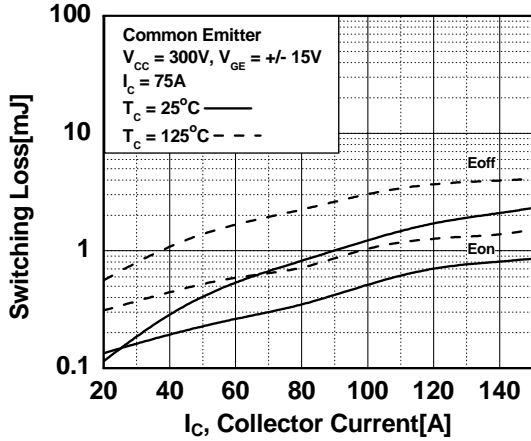


Fig 14. Gate Charge Characteristics

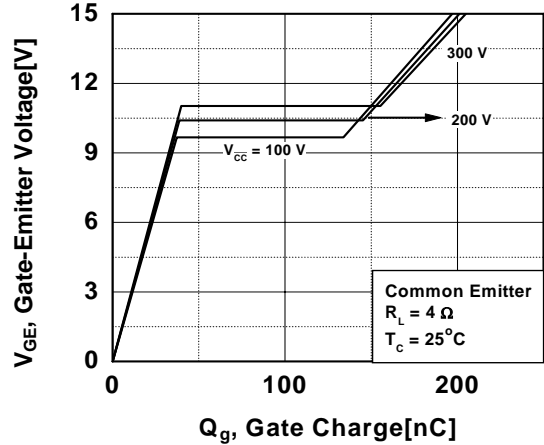


Fig 15. SOA Characteristics

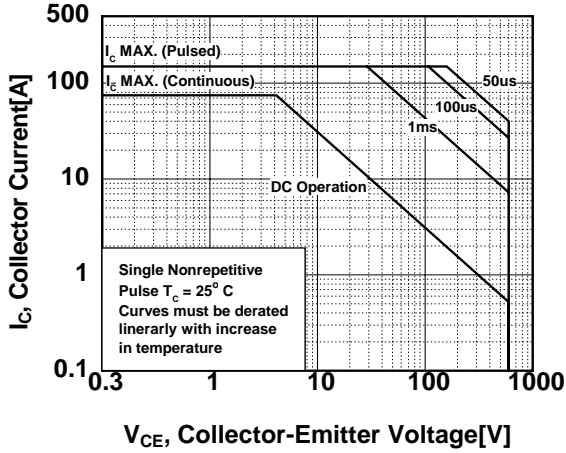


Fig 16. Turn-Off SOA Characteristics

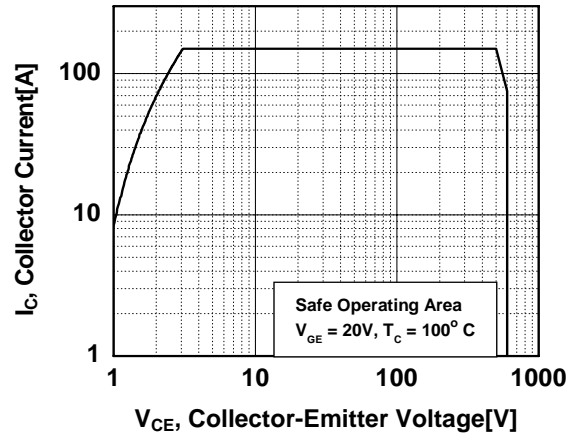


Fig 17. RBSOA Characteristics

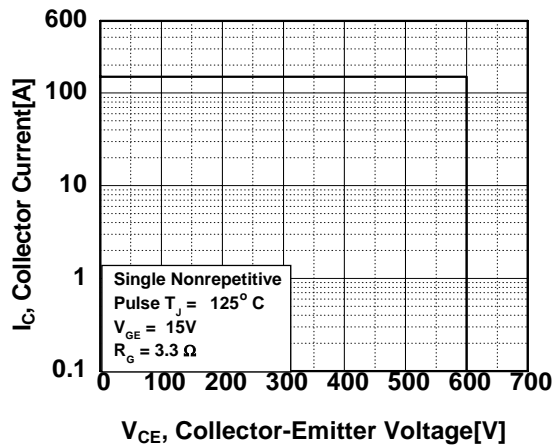


Fig 18. Transient Thermal Impedance

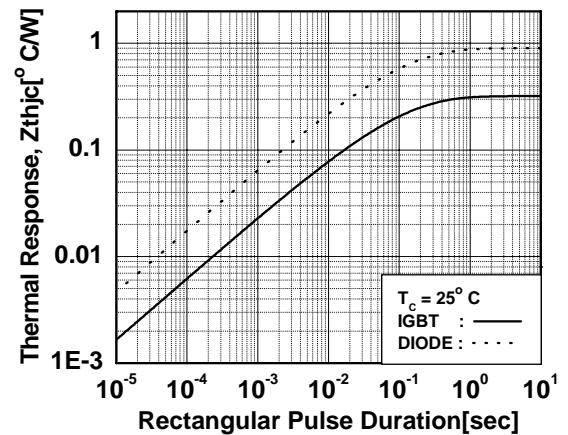


Fig 19. Forward Characteristics

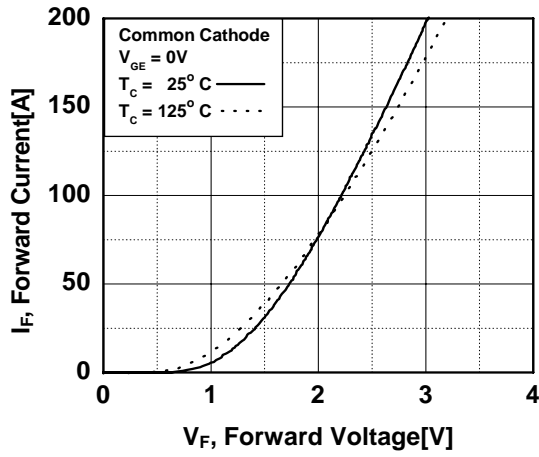
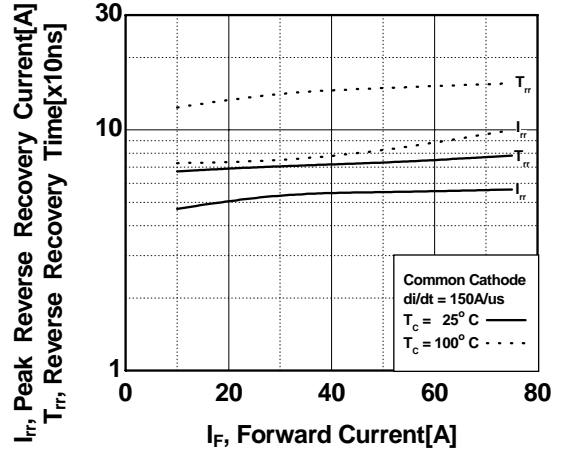
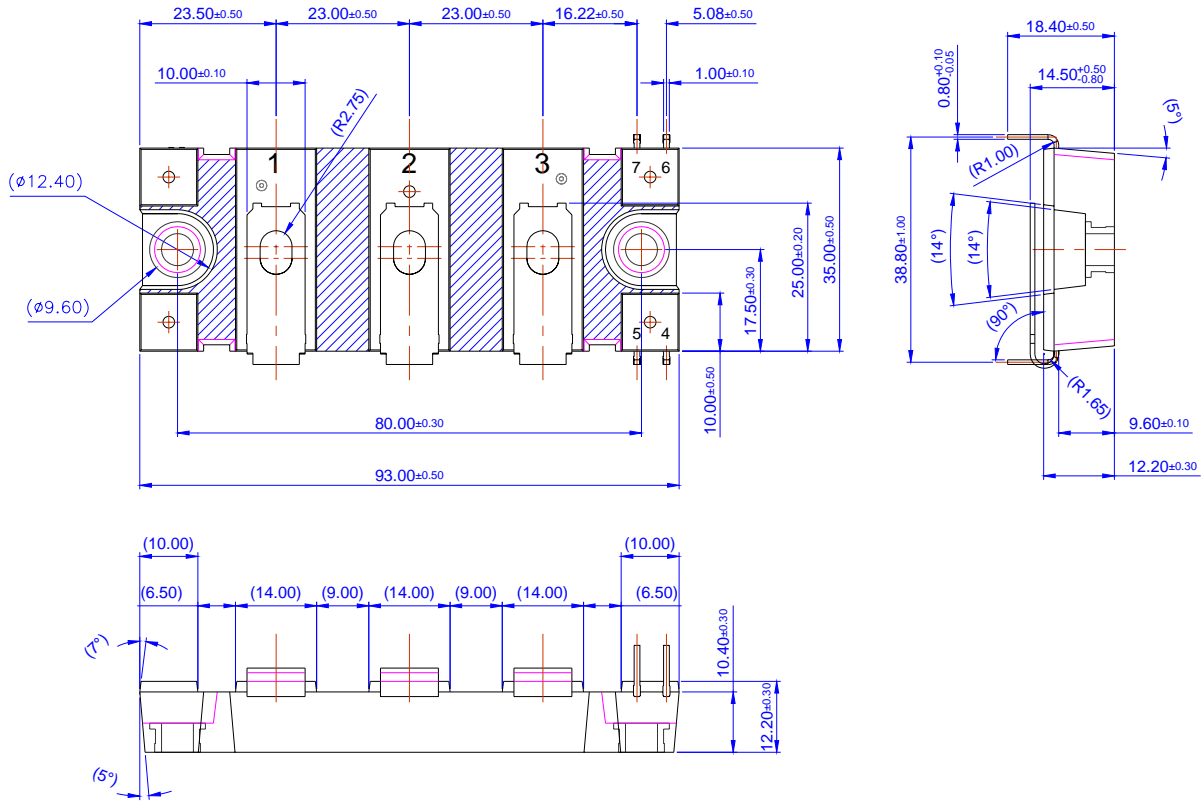


Fig 20. Reverse Recovery Characteristics












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